

FS10KMH-03

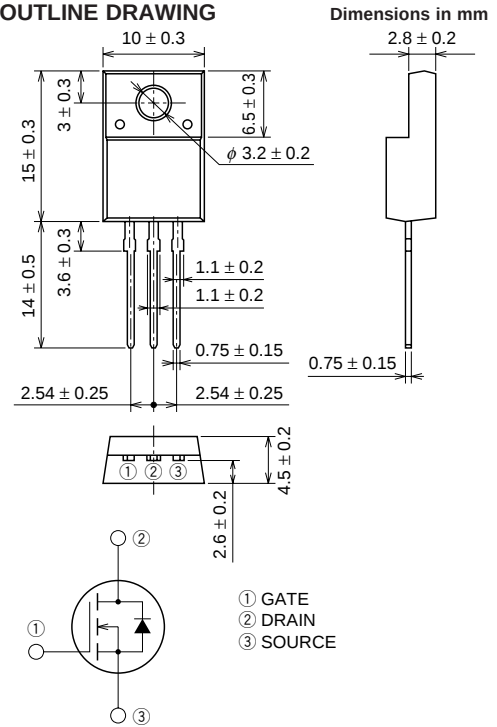
HIGH-SPEED SWITCHING USE

FS10KMH-03



- 2.5V DRIVE
- V_{DS} 30V
- $r_{DS(ON)} (MAX)$ 92m Ω
- I_D 10A
- Integrated Fast Recovery Diode (TYP.) 35ns
- V_{iso} 2000V

OUTLINE DRAWING



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

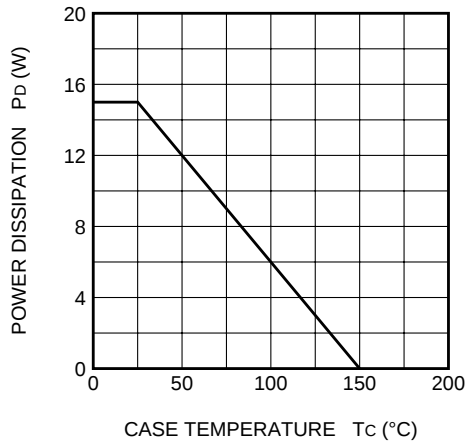
Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	30	V
V_{GS}	Gate-source voltage	$V_{DS} = 0V$	±10	V
I_D	Drain current		10	A
I_{DM}	Drain current (Pulsed)		40	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 30\mu H$	10	A
I_S	Source current		10	A
I_{SM}	Source current (Pulsed)		40	A
P_D	Maximum power dissipation		15	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
V_{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

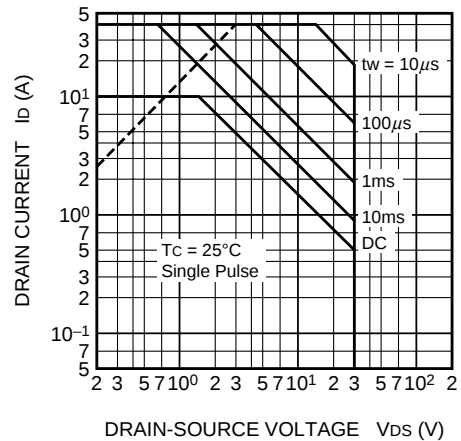
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±10V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 30V, V _{GS} = 0V	—	—	0.1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	0.6	0.9	1.2	V
r _{DS(ON)}	Drain-source on-state resistance	I _D = 5A, V _{GS} = 4V	—	68	92	mΩ
r _{DS(ON)}	Drain-source on-state resistance	I _D = 5A, V _{GS} = 2.5V	—	88	141	mΩ
V _{DS(ON)}	Drain-source on-state voltage	I _D = 5A, V _{GS} = 4V	—	0.34	0.46	V
y _{fs}	Forward transfer admittance	I _D = 5A, V _{DS} = 5V	—	12	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	540	—	pF
C _{oss}	Output capacitance		—	160	—	pF
C _{rss}	Reverse transfer capacitance		—	55	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 15V, I _D = 5A, V _{GS} = 4V, R _{GEN} = R _{GS} = 50Ω	—	12	—	ns
t _r	Rise time		—	35	—	ns
t _{d(off)}	Turn-off delay time		—	45	—	ns
t _f	Fall time		—	40	—	ns
V _{SD}	Source-drain voltage	I _S = 5A, V _{GS} = 0V	—	1.0	1.5	V
R _{th(ch-c)}	Thermal resistance	Channel to case	—	—	8.3	°C/W
t _{rr}	Reverse recovery time	I _S = 5A, di _s /dt = -50A/μs	—	35	—	ns

PERFORMANCE CURVES

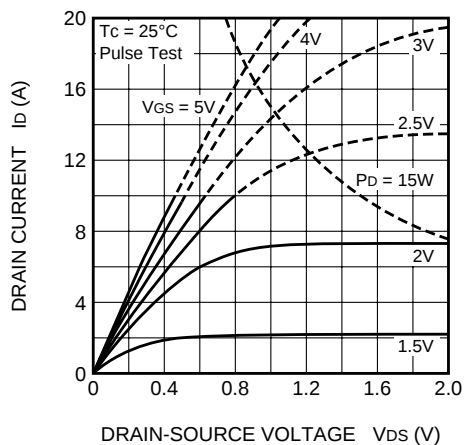
POWER DISSIPATION DERATING CURVE



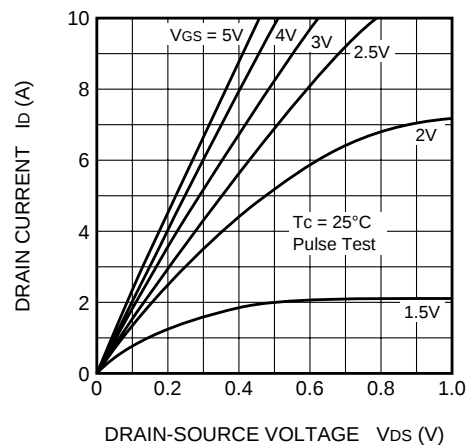
MAXIMUM SAFE OPERATING AREA



OUTPUT CHARACTERISTICS (TYPICAL)

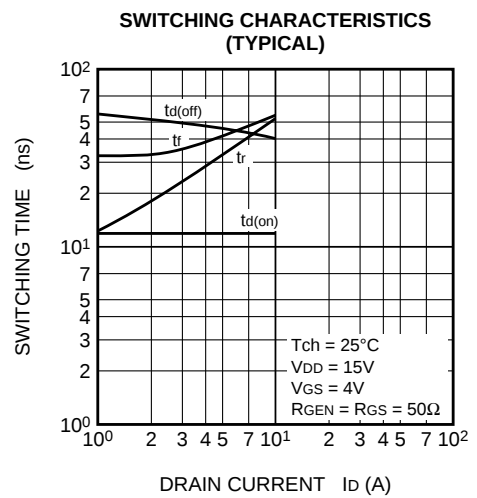
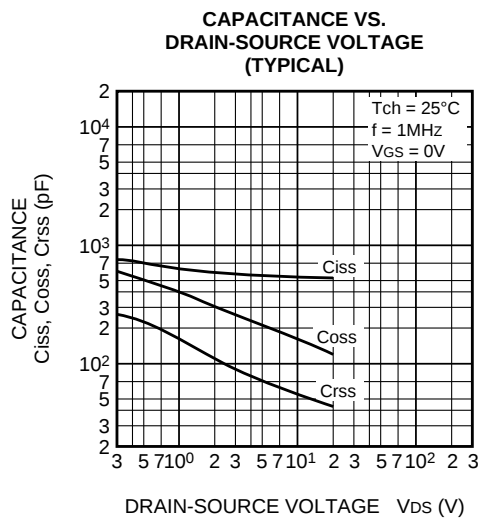
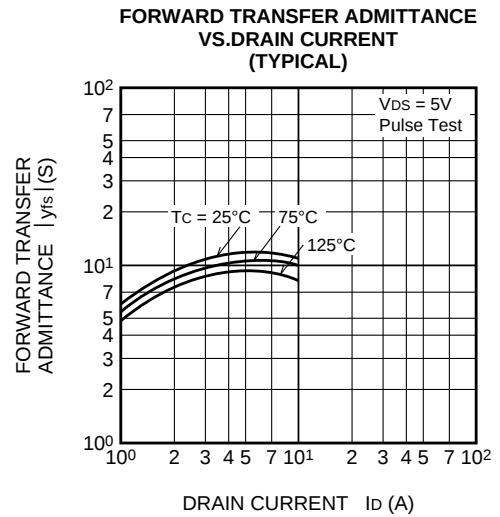
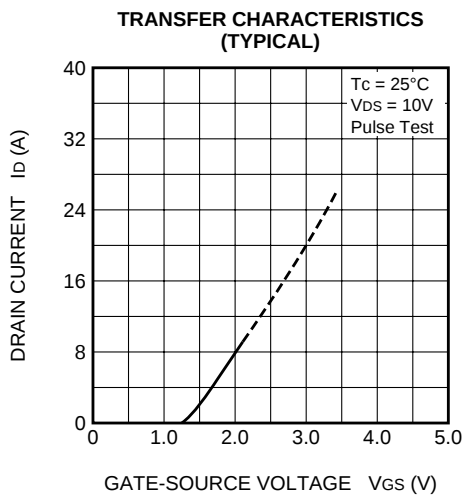
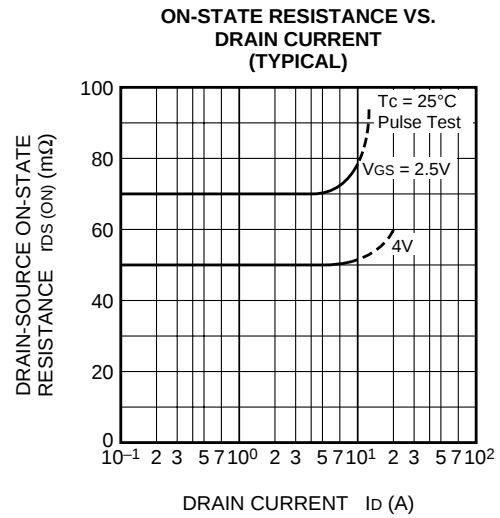
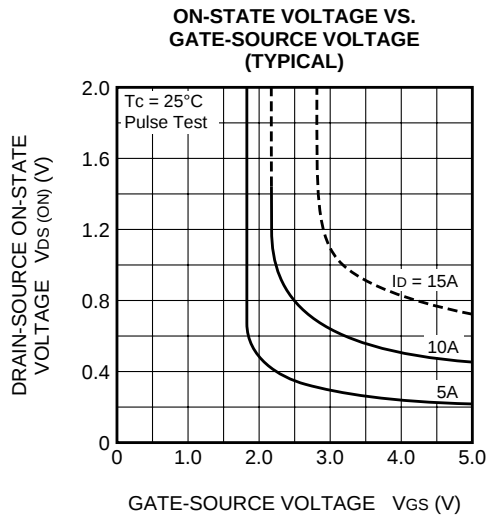


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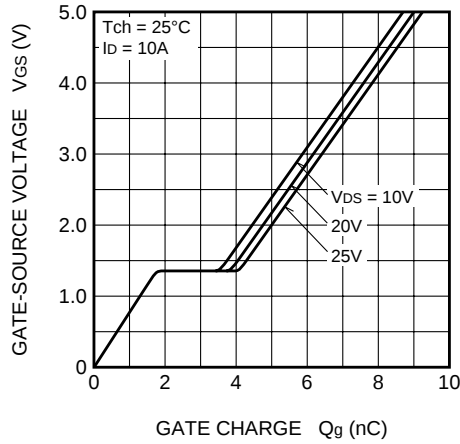


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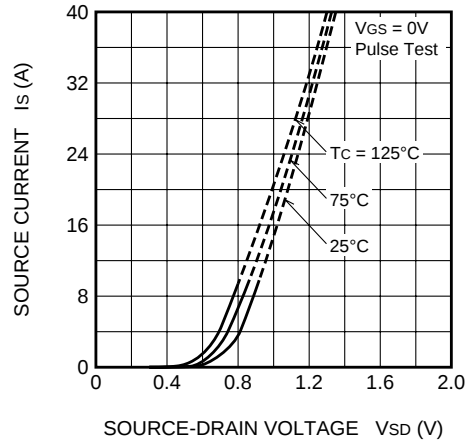
HIGH-SPEED SWITCHING USE



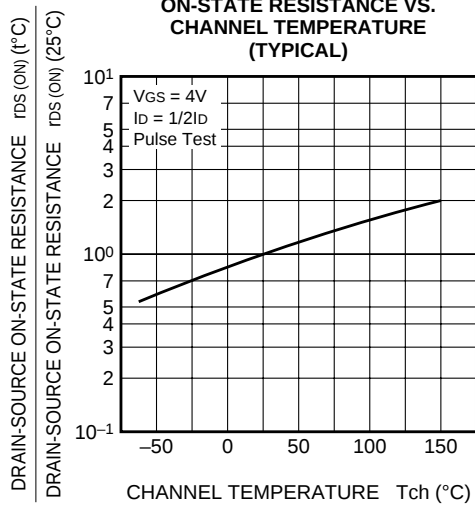
GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)



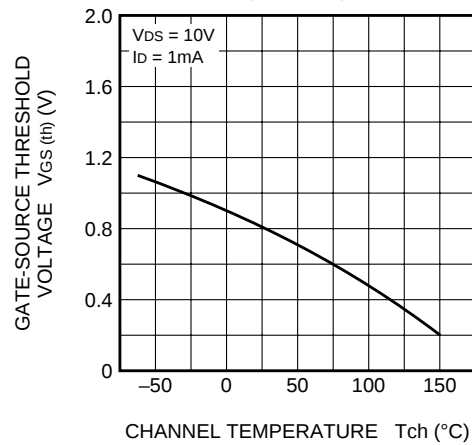
SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



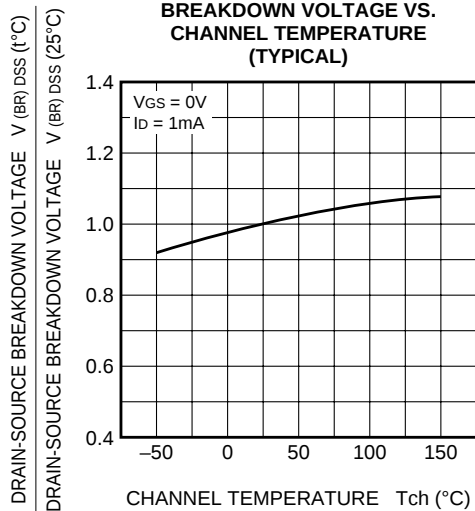
ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)



THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS

